



PTO/SB/08A (08-03)

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Substitute for form 1449/PTO		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(Use as many sheets as necessary)</i>		Application Number	10/760,549
		Filing Date	January 21, 2004
		First Named Inventor	Masayoshi TONOUCHI
		Art Unit	2829
		Examiner Name	J.M. HOLLINGTON
Sheet	1	of	2
		Attorney Docket Number	ASAIN0137

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear
		Country Code <sup>2</sup> Number <sup>4</sup> Kind Code <sup>3</sup> (if known)			
J. H.	A	JP 2000-036525	02-02-2000	NEC Corp.	_____
↓	B	JP 2000-311929	11-07-2000	NEC Corp.	_____

Examiner Signature	<i>John M. Higton</i>	Date Considered	8/2/05
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**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
A.H	C	Kiyoshi NIKAWA, "Failure Analysis in Si Device Chips." IEICE Trans. Electron, Vol. E77-C, No. 4, April 1994, pp. 528-534.	
	D	Hideo TODOKORO et al., "Electron-Beam LSI Tester." In "Semiconductor Technologies," J. Nishizawa (ed), Vo. 13, JARECT, 1984, pp. 373-382.	
↓	E	David H. AUSTIN et al., "Electrooptic Generation and Detection of Femtosecond Electrical Transients." IEEE J. Quantum Elec., Vol. 24, , No. 2, February 1988, pp. 184-197.	

Examiner Signature	<i>J. M. H</i>	Date Considered	8/2/05
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